

Multilayer Power Inductor

CIG32H2R2MNE (3225/ EIA 1210)

APPLICATION

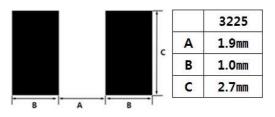
Mobile phones, DSC, DVC, PDA etc. for DC-DC Converter

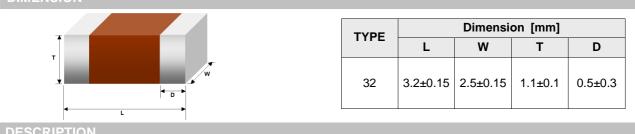
FEATURES

- High Current Type
- · Low DC resistance
- · Magnetically shielded structure
- Free of all RoHS-regulated substances
- · Monolithic structure for high reliability



RECOMMENDED LAND PATTERN



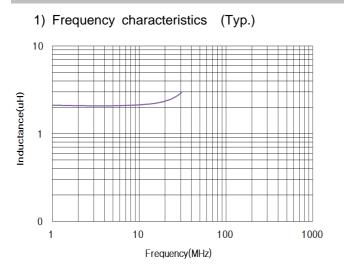


DESCRIPTION

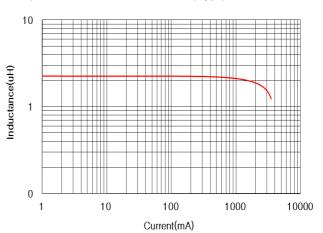
Dort no	Size	Inductance	DC	Rated Current (A)*1	Rated Current (A)*2
Part no.	(inch/mm)	(uH)@1MHz	Resistance(Ω)	Тур.	Max.
CIG32H2R2MNE	1210/3225	2.2±20%	0.125±25 %	2.90	1.60

**Operating temperature range: -40 to +125°C (Including self-temperature rise)
**Test equipment: Agilent :E4991A+16092A

CHARACTERISTIC DATA



2) DC Bias characteristics (Typ.)





CI G 32 H 2R2 M N E (1) (2) (3) (4) (5) (6) (7) (8)

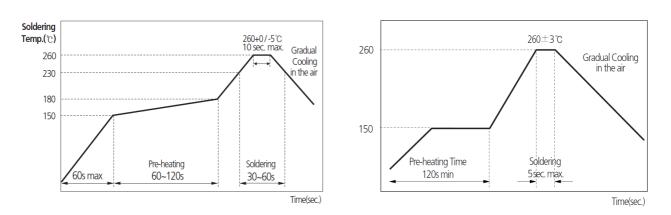
- (1) Chip Inductor
- (3) Dimension
- (5) Inductance (2R2:2.2uH)

- (2) Power Inductor
- (4) Product Series (H:High Current Type)

FLOW SOLDERING

- (6) Tolerance (M:±20%)
- (7) Thickness option(N:Standard, A:Thinner than standard, B:Thicker than standard)
- (8) Packaging(C:paper tape, E:embossed tape)

RECOMMENDED SOLDERING CONDITION



REFLOW SOLDERING

PACKAGING

Packaging Style	Quantity(pcs/reel)
Embossed Taping	2,500

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